

UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

~~MICRON TECHNOLOGY, INC., INTEL CORPORATION,
AND GLOBALFOUNDRIES U.S., INC.~~
Petitioners

SAMSUNG ELECTRONICS COMPANY, LTD.
Petitioner

v.

DANIEL L. FLAMM
Patent Owner

Case IPR. No. **Unassigned**
U.S. Patent No. 5,711,849

~~Title: PROCESS OPTIMIZATION IN GAS PHASE DRY ETCHING~~

~~Petition for *Inter Partes* Review of U.S. Patent No. 5,711,849 Under
35 U.S.C. §§ 311-319 and 37 C.F.R. §§ 42.1-.80, 42.100-
.123~~

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